TOSHIBA Transistor Silicon-Germanium NPN Epitaxial Planer Type

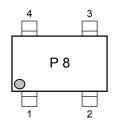
# MT4S102U

**UHF-SHF** Low Noise Amplifier Application

#### **FEATURES**

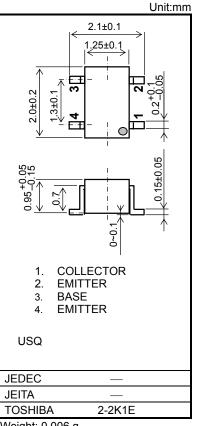
- Low Noise Figure :NF=0.58dB (@f=2GHz)
- High Gain:|S21e|2=15.0dB (@f=2GHz)

### Marking



#### **Absolute Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit
Collector-Base voltage	V <sub>CBO</sub>	6	V
Collector-Emitter voltage	V <sub>CEO</sub>	3	V
Emitter-Base voltage	V <sub>EBO</sub>	1.2	V
Collector-Current	IC	20	mA
Base-Current	I <sub>B</sub>	10	mA
Collector Power dissipation	PC	60	mW
Junction temperature	Tj	150	°C
Storage temperature Range	T <sub>stg</sub>	-55~150	°C



Weight: 0.006 g

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

# **Microwave Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> =2V, I <sub>C</sub> =15mA, f=2GHz	20	24	_	GHz
Insertion Gain	S21e  <sup>2</sup> (1)	V <sub>CE</sub> =2V, I <sub>C</sub> =15mA, f=2GHz	12.5	15.0	_	dB
	S21e  <sup>2</sup> (2)	V <sub>CE</sub> =2V, I <sub>C</sub> =15mA, f=5.2GHz	_	8.0	_	dB
Noise Figure	NF(1)	V <sub>CE</sub> =2V, I <sub>C</sub> =10mA, f=2GHz	_	0.58	0.85	dB
	NF(2)	V <sub>CE</sub> =2V, I <sub>C</sub> =10mA, f=5.2GHz	_	1.4	_	dB

# **Electrical Characteristics (Ta = 25°C)**

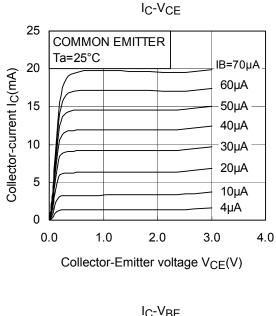
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector Cut-off Current	I <sub>CBO</sub>	V <sub>CB</sub> =6V, I <sub>E</sub> =0	_	_	1	μA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> =1V, I <sub>C</sub> =0	_	_	1	μA
DC Current Gain	hFE	V <sub>CE</sub> =2V, I <sub>C</sub> =15mA	200	_	400	-
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =2V, I <sub>E</sub> =0, f=1MHz	_	0.43	0.6	pF
Reverse Transfer Capacitance	C <sub>re</sub>	V <sub>CB</sub> =2V, I <sub>E</sub> =0, f=1MHz (Note 1)	_	0.17	0.25	pF

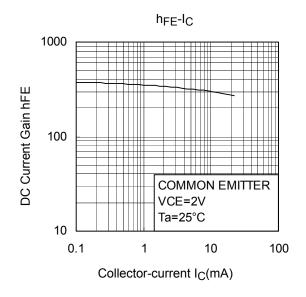
**Note 1:** Cre is measured by 3 terminal method with capacitance bridge.

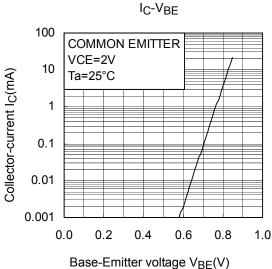
#### Caution:

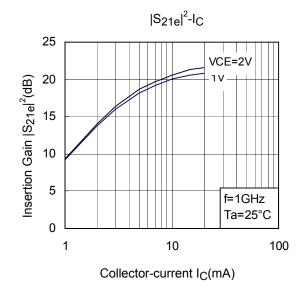
This device is sensitive to electrostatic discharge due to applied the high frequency transistor process of fT=60GHz class is used for this product.

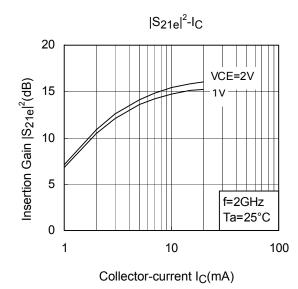
Please make enough tool and equipment earthed when you handle.

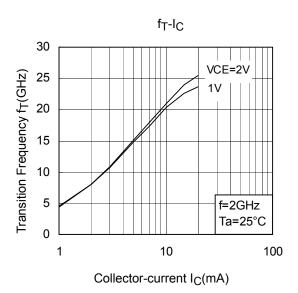




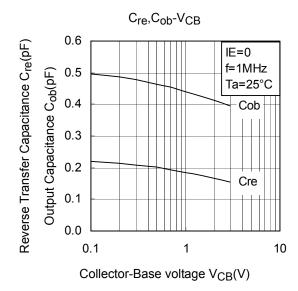


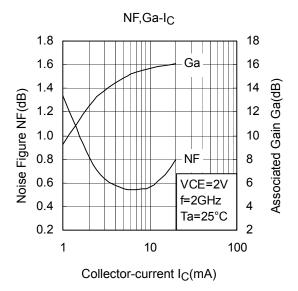


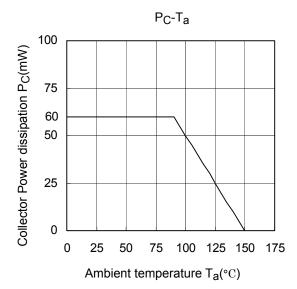




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